

General Description

This device has been developed using Trench technology, these products have been designed to minimize on-state resistance and fast switching performance. These products are suited for load switch and protection applications.

Features

- Low On-Resistance
- High Current Capability
- RoHS Compliant and Halogen Free

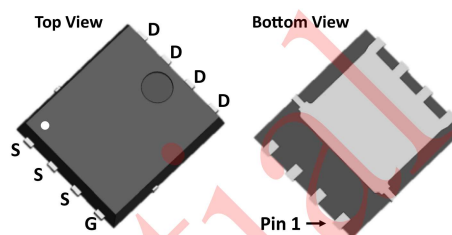
Applications

- Load Switch
- Battery Protection
- Reverse Protection

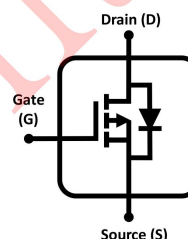
30V P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max.	I_D
-30 V	3.3 m Ω @ -10 V	-100 A
	5.0 m Ω @ -4.5 V	

PPAK5x6



Pin Configuration



Absolute Maximum Ratings (T_J=25°C, unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{DS}	Drain-Source Voltage		-30	V
V _{GS}	Gate-Source Voltage		±20	
I _D	Drain Current-Continuous ^A	T _A =25 °C	-16	A
		T _A =70 °C	-12.5	
		T _C =25 °C	-100	
		T _C =100 °C	-63.2	
I _{DM}	Drain Current-Pulsed ^{A, B}	T _C =25°C	-400	A
I _{AS}	Non-repetitive Avalanche Current ^E		-80	A
E _{AS}	Single Pulse Drain-to-Source Avalanche Energy ^E		320	mJ
P _D	Maximum Power Dissipation	T _C =25 °C	138	W
		T _C =100 °C	55	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Junction-to-Ambient ^C	Steady State	62	°C/W
$R_{\theta JC}$	Junction-to-Case	Steady State	0.9	°C/W